



30V N-Channel Enhancement Mode MOSFET

Voltage

30 V

Current

60 A

Features

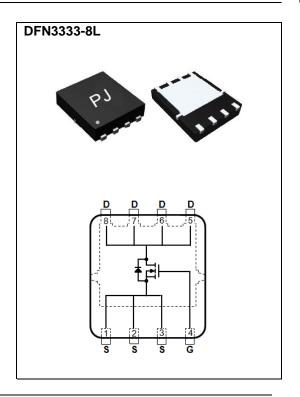
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@10A<6m\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_D@8A<9m\Omega$
- High switching speed
- Improved dv/dt capability
- Low gate charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.001 ounces, 0.03 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

| PARAMETER | | SYMBOL | LIMIT | UNITS | |
|--|----------------------|---------------------|-------------|----------|--|
| Drain-Source Voltage | | V _{DS} | 30 | V | |
| Gate-Source Voltage | | V _{GS} | <u>+</u> 20 | V | |
| Continuous Drain Current | Tc=25°C | I _D | 60 | А | |
| | Tc=100°C | | 38 | | |
| Pulsed Drain Current(Note 1) | Tc=25°C | I _{DM} | 240 | <u> </u> | |
| Power Dissipation | Tc=25°C | Po | 31 | W | |
| | Tc=100°C | | 12.4 | | |
| Continuous Drain Current | T _A =25°C | Ι _D | 15 | А | |
| | T _A =70°C | | 12 | Α | |
| Power Dissipation | T _A =25°C | - | 2.0 | W | |
| Power Dissipation | T _A =70°C | Pb | 1.3 | | |
| Operating Junction and Storage Temperature Range | | T_{J} , T_{STG} | -55~150 | °C | |
| Typical Thermal Resistance ^(Note 4,5) | Junction to Case | $R_{	heta JC}$ | 4.0 | °C/W | |
| | Junction to Ambient | $R_{\theta JA}$ | 62.5 | | |

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25°C unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNITS |
|----------------------------------|---------------------|---|------|------|--------------|-------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V,I _D =250uA | 30 | - | - | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | V _{DS} =V _{GS} ,I _D =250uA | 1.0 | 1.6 | 2.5 | V |
| Drain-Source On-State Resistance | R _{DS(on)} | V _{GS} =10V,I _D =10A | - | 5 | 6 | mΩ |
| | | V _{GS} =4.5V,I _D =8A | - | 6.6 | 9 | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =30V,V _{GS} =0V | - | - | 1.0 | uA |
| Gate-Source Leakage Current | Igss | V _{GS} = <u>+</u> 20V,V _{DS} =0V | - | - | <u>+</u> 100 | nA |
| Dynamic ^(Note 6) | | | | | | |
| Total Gate Charge | Q_g | V _{DS} =15V, I _D =20A, V _{GS} =4.5V ^(Note 1,2) | - | 12 | - | nC |
| Gate-Source Charge | Qgs | | - | 3.8 | - | |
| Gate-Drain Charge | Q_{gd} | | - | 4.3 | - | |
| Input Capacitance | Ciss | V _{DS} =25V, V _{GS} =0V, | - | 1323 | - | pF |
| Output Capacitance | Coss | | - | 219 | - | |
| Reverse Transfer Capacitance | Crss | f=1.0MHZ | - | 136 | - | |
| Turn-On Delay Time | td _(on) | $V_{DS}{=}15V,RL{=}1\Omega,$ $V_{GS}{=}10V,~R_{G}{=}3.3\Omega$ (Note 2,3) | - | 5.0 | - | ns |
| Turn-On Rise Time | tr | | - | 42 | - | |
| Turn-Off Delay Time | td _(off) | | - | 36 | - | |
| Turn-Off Fall Time | t _f | | - | 5.5 | - | |
| Drain-Source Diode | | | | | | |
| Maximum Continuous Drain-Source | , | | - | - | 60 | А |
| Diode Forward Current | Is | | | | | |
| Diode Forward Voltage | V _{SD} | I _S =1A,V _{GS} =0V | - | 0.83 | 1 | V |

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

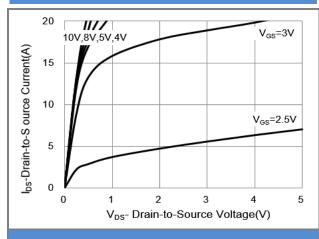


Fig.1 On-Region Characteristics

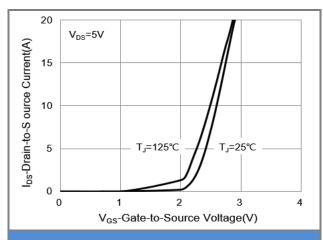


Fig.2 Transfer Characteristics

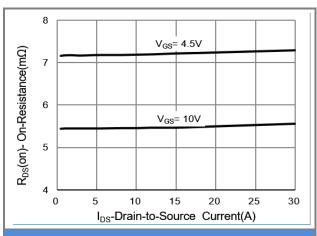


Fig.3 On-Resistance vs. Drain Current

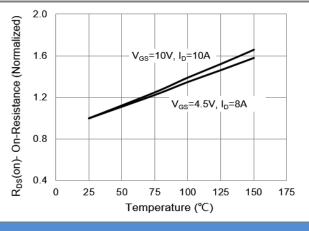


Fig.4 On-Resistance vs. Junction temperature

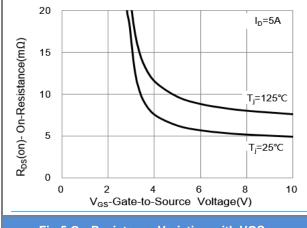


Fig.5 On-Resistance Variation with VGS.

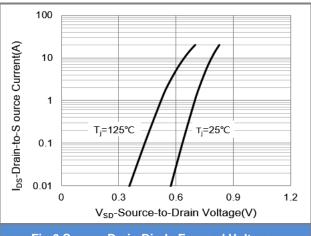


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

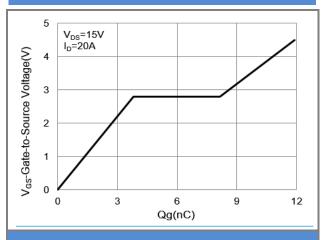
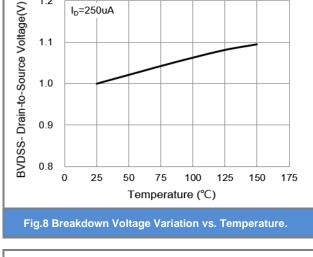


Fig.7 Gate-Charge Characteristics



1.2

I_D=250uA

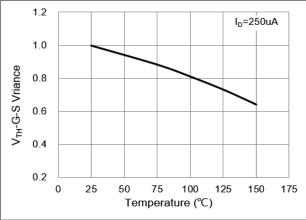


Fig.9 Threshold Voltage Variation with Temperature

Notes: 1. Tj=150°C 2. Tc=25℃ 3. Single pulse

V_{DS}-Drain-Source Voltage (V)

Fig.11 Maximum Safe Operating Area

10

Operation this area is Limited by R_{DS(ON)}

1000

100

10

0.1

l_{DS}-Drain-to-S ource Current(A)



2000 $V_{GS} = 0V$ f = 1MHz 1500 Ciss Capicitance (pF) 1000 500 Coss Crss 0 0 10 20 30 V_{DS}-Drain-Source Voltage (V)

Fig.10 Capacitance vs. Drain-Source Voltage.





TYPICAL CHARACTERISTIC CURVES

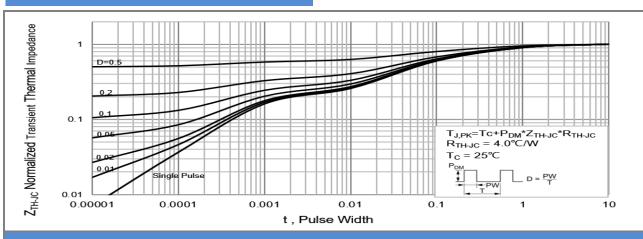


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

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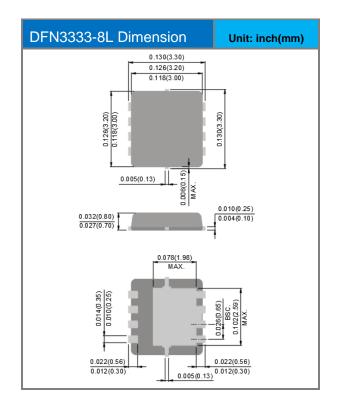


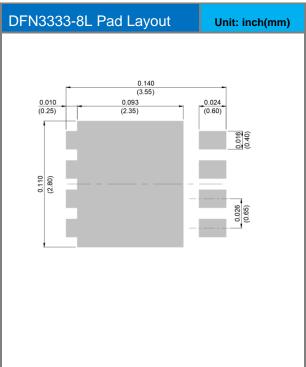


Part No. Packing Code Version

| Part No. Packing Code | Package Type | Packing Type | Marking | Version |
|-----------------------|--------------|-------------------|---------|--------------------------------|
| PJQ4404P_R2_00001 | DFN3333-8L | 5K pcs / 13" reel | 4404 | Halogen free RoHS compliant |

Packaging Information & Mounting Pad Layout









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